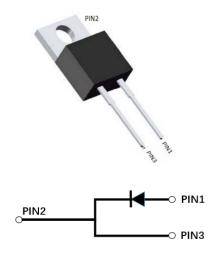




# **Silicon Carbide Schottky Diode**

$V_{RRM}$	650V
I <sub>F(135°C)</sub>	6.5A
Q <sub>C</sub>	12.5nC



#### **Features**

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- AEC-Q101 qualified
- High-frequency operation
- Reduction of EMI

## **Typical Applications**

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

#### **Mechanical Data**

• Package: TO-220AC

Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free

• Terminals: Tin plated leads

• Polarity: As marked

## ■Maximum Ratings (T<sub>C</sub>=25°C Unless otherwise specified)

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D106504PG1
Reverse voltage (Repetitive peak) @ T <sub>j</sub> =25°C	$V_{RRM}$	٧	650
Reverse voltage (Surge peak) @ T <sub>j</sub> =25°C	$V_{RSM}$	V	650
Reverse voltage (DC) @ T <sub>j</sub> =25°C	$V_{DC}$	V	650
Continuous forward current @ T <sub>C</sub> =25°C		А	14
Continuous forward current @ T <sub>C</sub> =135°C	I <sub>F</sub>		6.5
Continuous forward current @ T <sub>C</sub> =158°C			4
Non-repetitive peak forward surge current @ T <sub>C</sub> =25°C, tp=10ms, Half Sine Wave	I <sub>FSM</sub>	А	32
Power Dissipation@ T <sub>C</sub> =25°C	P <sub>TOT</sub>	W	60
Power Dissipation@ T <sub>C</sub> =110°C	Гтот	VV	26
i²t Value@ T <sub>C</sub> =25°C ,tp=10ms	∫ i²dt	A <sup>2</sup> S	5.1
Operating junction and Storage temperature range	$T_{j}$ , $T_{stg}$	°C	-55 to +175



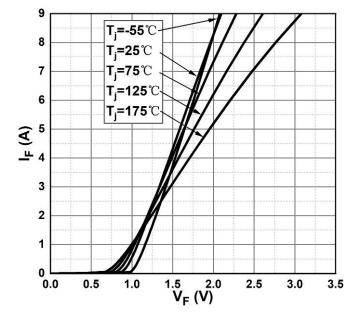
### **■**Electrical Characteristics

PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.
Forward voltage drop	V <sub>F</sub>	>	I <sub>F</sub> =4A, T <sub>j</sub> =25°C	1.46	1.55
			I <sub>F</sub> =4A, T <sub>j</sub> =175°C	1.75	-
Reverse leakage current	I <sub>R</sub>	μА	V <sub>R</sub> =650V, T <sub>j</sub> =25°C	0.5	20
			V <sub>R</sub> =650V, T <sub>j</sub> =175°C	30	-
Total capacitive charge	Q <sub>C</sub>	nC	$V_R$ =400V, $T_j$ =25°C , $Q_C$ = $\int_0^{VR} C(V) dV$	12.5	-
Total capacitance	С	pF	V <sub>R</sub> =0V, f=1MHZ	266	-
			V <sub>R</sub> =200V, f=1MHZ	24	-
			V <sub>R</sub> =400V, f=1MHZ	19	-
Capacitance Stored Energy	Ec	μJ	V <sub>R</sub> =400V	1.6	-

# **■Thermal Characteristics** (T<sub>a</sub>=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	$R_{\theta J-C}$	°C W	2.47

# **■**Typical Characteristics





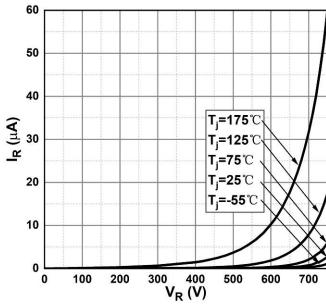
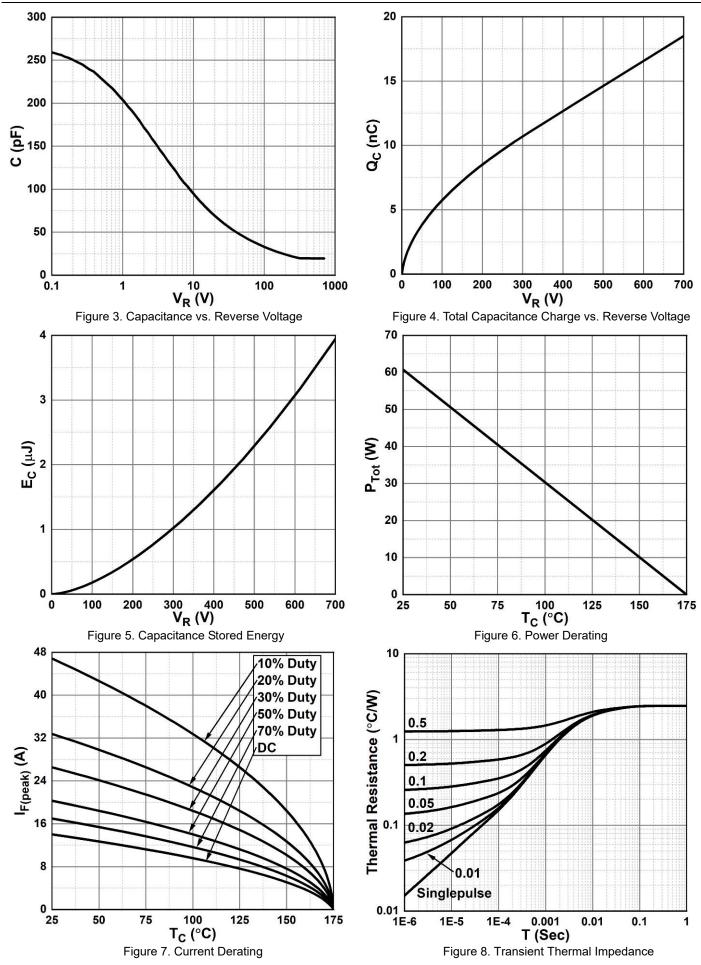


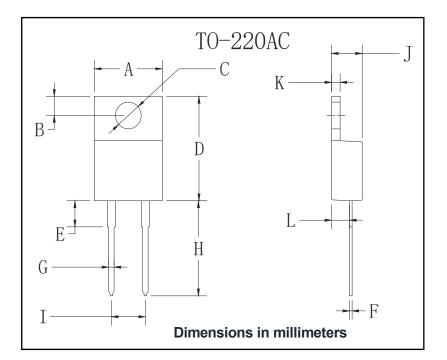
Figure 2. Reverse Characteristics







## **■**Outline Dimensions



TO-220AC				
Dim	Min	Max		
Α	9.95	10.35		
В	2.55	2.95		
С	3.75	4.05		
D	14.95	15.25		
E	3.75	4.25		
F	0.26	0.5		
G	0.68	0.94		
Н	13.3	13.9		
I	4.86	5.26		
J	4.38	4.78		
K	1.14	1.4		
L	2.37	2.79		



# YJD106504PG1Q



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